

Atty Docket No.: JCLA8894

Serial No.: 10/084,761

A2
B1
3. (Once Amended) A substrate cutting method as set forth in Claim 1, characterized in that a surface layer of the substrate is irradiated with said laser.

A3
B1
11. (Once Amended) A substrate cutting method as set forth in Claim 10, characterized in that the thickness of said semiconductor wafer is equal to or less than 50 μ m.